METHOD FOR FORMING PATTERNS FOR SEMICONDUCTOR DEVICES

Abstract of the Disclosure

A method for forming an electrically conductive layer having predetermined patterns for semiconductor devices includes providing a substrate, forming an insulation layer having OH functional groups on the substrate, forming a patterned polymer layer on the insulation layer, etching the insulation layer to create a patterned insulation layer which has the same patterns as the patterned polymer layer, stripping the patterned polymer layer to expose the patterned insulation layer, treating the patterned insulation layer with a coupling agent which reacts with the OH functional groups, treating the patterned insulation layer with a catalyst-containing solution in which the catalyst reacts with the coupling agent, and depositing electrically conductive material on the patterned insulation layer which is catalytically active.

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